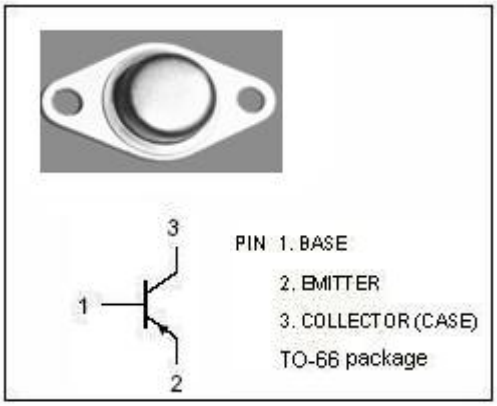
isc Silicon PNP Power Transistor BDX14

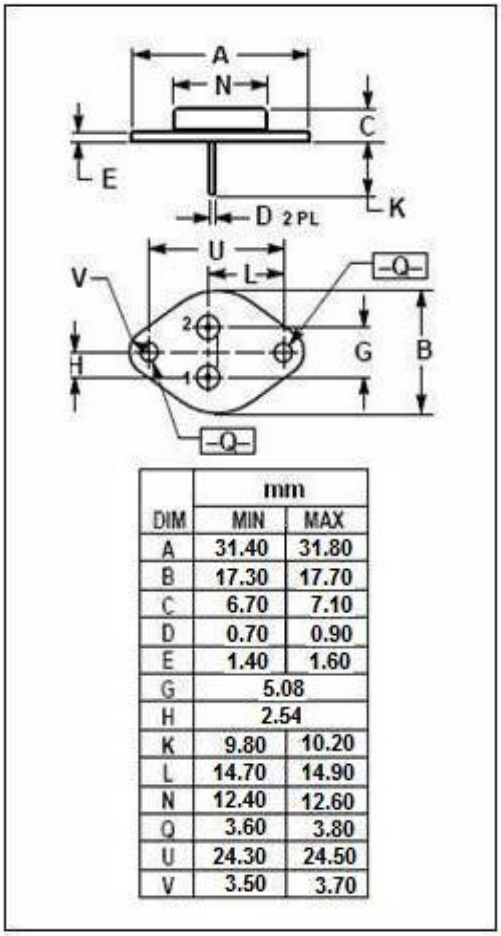
DESCRIPTION

- Continuous Collector Current-I_C= -4A
- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= -55V(Min.)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for general purpose switching and amplifier applications.



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-90	V
V_{CER}	Collector-Emitter Voltage R_{BE}= 100Ω	-60	V
V_{CEO}	Collector-Emitter Voltage	-55	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-4	A
I_B	Base Current-Continuous	-2	A
P_C	Collector Power Dissipation@T_C=25℃	29	W
T_J	Junction Temperature	200	℃
T_{stg}	Storage Temperature	-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	6.0	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -30mA; I_B= 0	-55		V
$V_{CER(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -100mA; R_{BE}= 100Ω	-60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -1mA; I_C= 0	-7		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA		-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -0.5A; V_{CE}= -4V		-1.7	V
I_{CEX}	Collector Cutoff Current	V_{CE}= -90V; V_{BE}= 1.5V V_{CE}= -30V; V_{BE}= 1.5V,T_C=150℃		-1.0 -5.0	mA
h_{FE}	DC Current Gain	I_C= -0.5A; V_{CE}= -4V	25	100	
f_T	Current Gain-Bandwidth Product	I_C= -0.2A; V_{CE}= -10V	4		MHz